

## IN THE CLAIMS

Claims 1-12 have been canceled without prejudice.

Please amend claims 13 and 16.

Please enter the pending claims as follows:

1.-12. (Canceled)

13. (Currently Amended) A method comprising:

- providing a substrate;
- forming a layer over said substrate;
- patterning said layer into a first region and a second region;
- removing said layer in said first region;
- inspecting said first region for an opaque defect;
- forming a reactant gas over said opaque defect; and
- directing electrons toward said opaque defect, said electrons inducing said

reactant gas to etch said opaque defect without ion bombardment.

14. (Original) The method of claim 13 wherein said reactant gas etches said opaque defect without damage to said substrate.

15. (Original) The method of claim 13 wherein said opaque defect comprises chrome and said reactant gas comprises chlorine and oxygen.

16. (Currently Amended) A method comprising:

providing a substrate;

forming a mirror over said substrate;

forming a buffer layer over said mirror;

forming an absorber layer over said buffer layer;

patterning said absorber layer into a first region and a second region;

removing said absorber layer in said first region;

inspecting said first region for an opaque defect;

dispensing a reactant gas over said opaque defect; and

scanning an electron beam over said opaque defect, said electron beam

inducing said reactant gas to react with said opaque defect without ion bombardment to form a volatile byproduct.

17. (Original) The method of claim 16 wherein said opaque defect comprises an absorber and said reactant gas comprises Xenon Fluoride ( $\text{XeF}_2$ ).